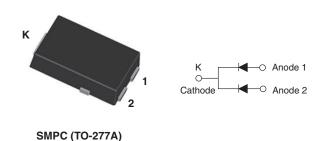
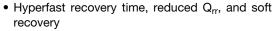
# Hyperfast Rectifier, 2 x 3 A FRED Pt®



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 x 3 A			
$V_R$	100 V			
V <sub>F</sub> at I <sub>F</sub>	0.75 V			
t <sub>rr (typ.)</sub>	27 ns			
T <sub>J</sub> max.	175 °C			
Package	SMPC (TO-277A)			
Circuit configuration	Dual serial			

#### **FEATURES**





RoHS

COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		$V_{RRM}$		100	V
A	per device	I <sub>F(AV)</sub>	T - 165 °C	6	A
Average rectified forward current	per diode		T <sub>Sp</sub> = 165 °C	3	
Non-repetitive peak surge current	per device		T 05 %C C	150	
	per diode	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	80	
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	100	-	-	
	age, per diode V <sub>F</sub>	I <sub>F</sub> = 3 A	-	0.87	0.94	V
Forward voltage, per diode		I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.75	0.79	
Reverse leakage current, per diode I <sub>R</sub>		V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	
	IR	T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	0.7	10	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 100 V	-	13	-	pF



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	27	-	
Reverse recovery time t <sub>rr</sub>	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	25	
	L <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	20	-	ns
	T <sub>J</sub> = 125 °C		-	26	-		
Peak recovery current I <sub>RRM</sub>	1	T <sub>J</sub> = 25 °C	$I_F=3$ A $dI_F/dt=200$ A/ $\mu$ s $V_R=160$ V	-	2.4	-	Α
	T T	T <sub>J</sub> = 125 °C		-	3.8	-	A
Deverse receivery charge	0	T <sub>J</sub> = 25 °C		-	23	-	nC
neverse recovery charge	Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	50	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to solder pad, per diode	R <sub>thJ-Sp</sub>		-	2.8	4	°C/W
Approximate weight				0.1		g
Approximate weight				0.0035		oz.
Marking device		Case style SMPC (TO-277A)		NC	H1	

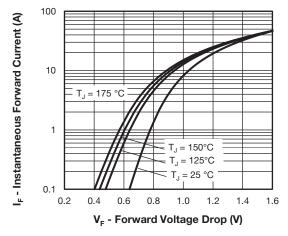


Fig. 1 - Typical Forward Voltage Drop Characteristics

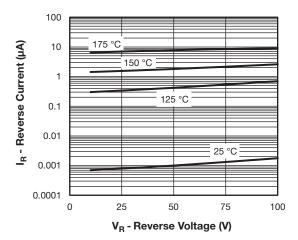


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

### www.vishay.com

## Vishay Semiconductors

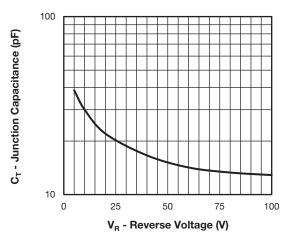


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

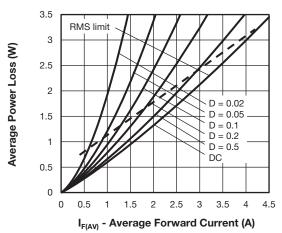


Fig. 5 - Forward Power Loss Characteristics

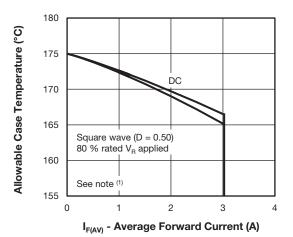


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

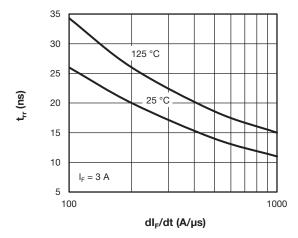


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

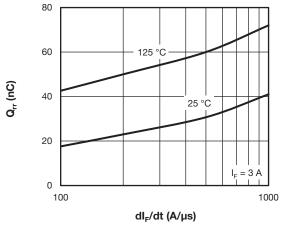
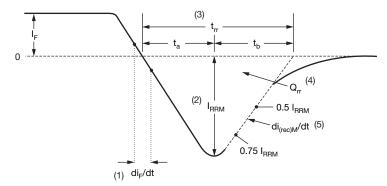


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ \text{(see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \ \text{(1 - D)}; \ I_R \ \text{at} \ V_{R1} = \text{rated} \ V_R \\ \end{array}$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{r}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

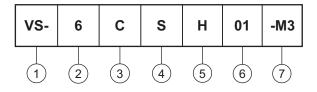
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

#### **Device code**



- Vishay Semiconductors product
- 2 Current rating (6 = 6 A)
- 3 Circuit configuration:

C = common cathode

- S = SMPC package

5 - Process type,

H = hyper fast recovery

Voltage code (01 = 100 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

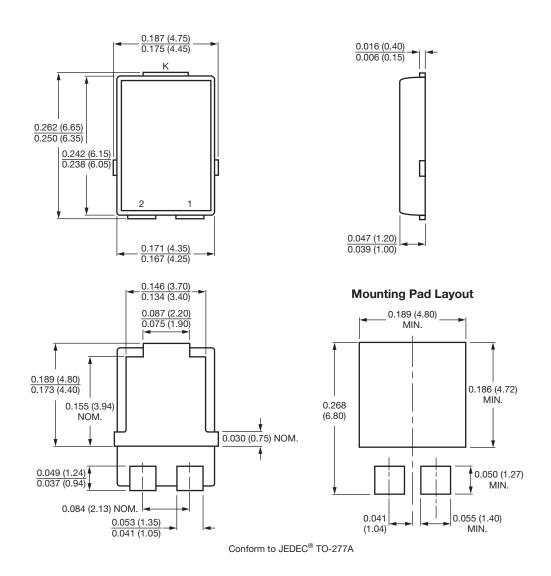
ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-6CSH01-M3/86A	1500	1500	7" diameter plastic tape and reel	
VS-6CSH01-M3/87A	6500	6500	13" diameter plastic tape and reel	

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95570</u>				
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96378			



# **TO-277A (SMPC)**

### **DIMENSIONS** in inches (millimeters)





### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.